

MIYASHITA ET AL. -- 09/916,530
Client/Matter: 008312-0279038

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1.-10. (Cancelled)

11. (Currently Amended) A method of manufacturing a semiconductor device, comprising:

forming a gate insulating film on a semiconductor substrate;

forming a gate electrode on the gate insulating film;

forming a source-drain diffusion layer in the semiconductor substrate;

forming a ~~film which inhibits silicidation~~ an oxide film on the source-drain diffusion layer;

forming a film of a metal having a high melting point on the gate electrode and on the ~~source-drain diffusion layer~~ oxide film; and

converting the film of the high melting point metal into a silicide film to form a first silicide film on the source-drain diffusion layer and a second silicide film on the gate electrode, the second silicide film having a thickness greater than that of the first silicide film.

12. (Canceled)

13.-19. (Cancelled)

20. (Previously Presented) A method of manufacturing a semiconductor device, comprising:

forming a gate insulating film on a semiconductor substrate;

forming a gate electrode on the gate insulating film;

forming a source-drain diffusion layer in the semiconductor substrate;

introducing into the source-drain diffusion layer atoms which inhibits silicidation;

forming a film of a metal having a high melting point on the gate electrode and the source-drain diffusion layer; and

MIYASHITA ET AL. -- 09/916,530
Client/Matter: 008312-0279038

converting the film of the high melting point metal into a silicide film to form a first silicide film on the source-drain diffusion layer and a second silicide film on the gate electrode, the second silicide film having a thickness greater than that of the first silicide film.

21. (Previously Presented) The method of manufacturing a semiconductor device according to claim 20, wherein said atoms serving to inhibit said silicidation is selected from the group consisting of fluorine, nitrogen and oxygen.